
2SB715, 2SB716, 2SB716A

Silicon PNP Epitaxial

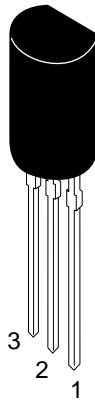
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Application

- Low frequency high voltage amplifier
- Complementary pair with 2SD755, 2SD756 and 2SD756A

Outline

TO-92MOD



1. Emitter
2. Collector
3. Base

2SB715, 2SB716, 2SB716A

Absolute Maximum Ratings (Ta = 25°C)

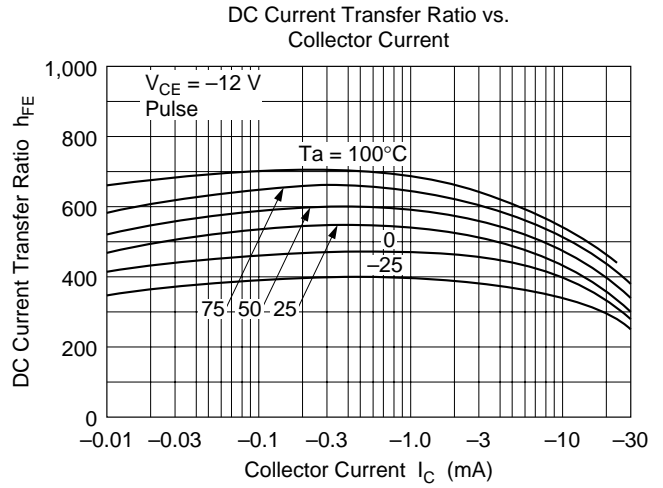
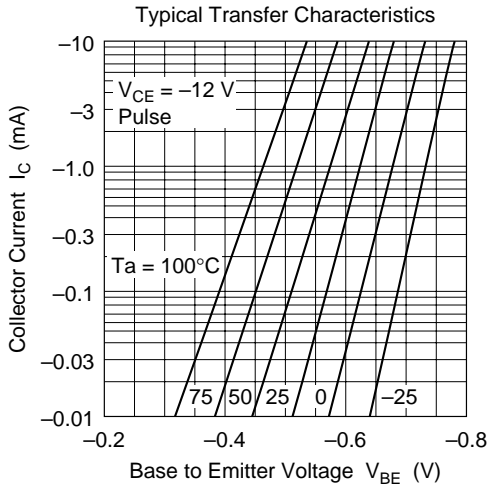
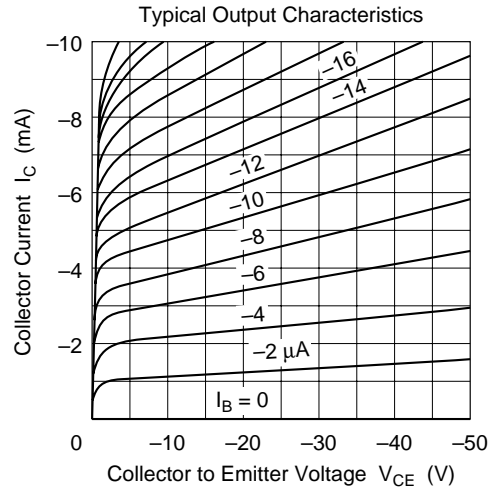
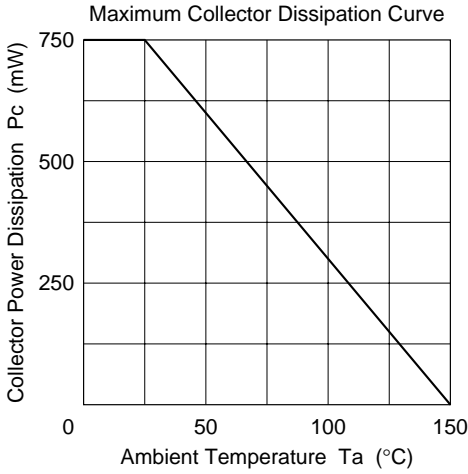
Item	Symbol	2SB715	2SB716	2SB716A	Unit
Collector to base voltage	V_{CBO}	-100	-120	-140	V
Collector to emitter voltage	V_{CEO}	-100	-120	-140	V
Emitter to base voltage	V_{EBO}	-5	-5	-5	V
Collector current	I_C	-50	-50	-50	mA
Collector power dissipation	P_C	750	750	750	mW
Junction temperature	T_j	150	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

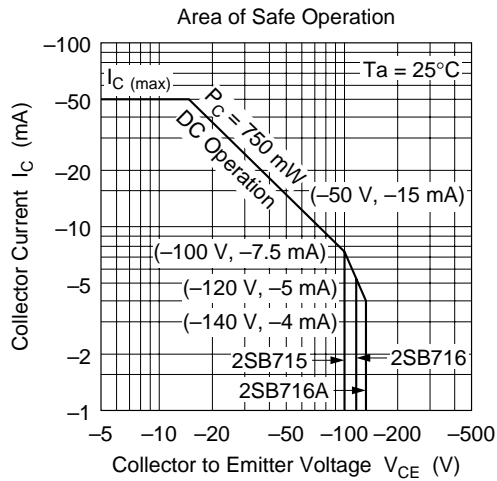
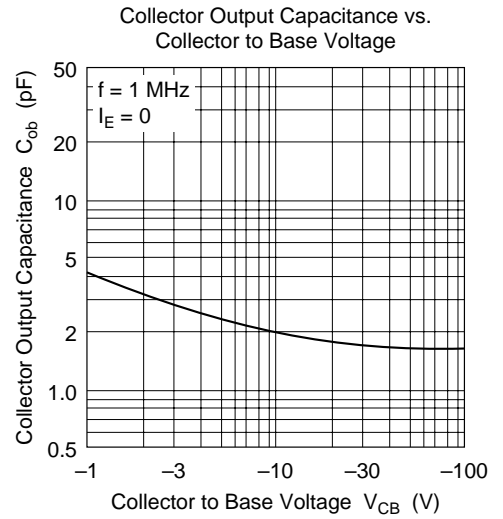
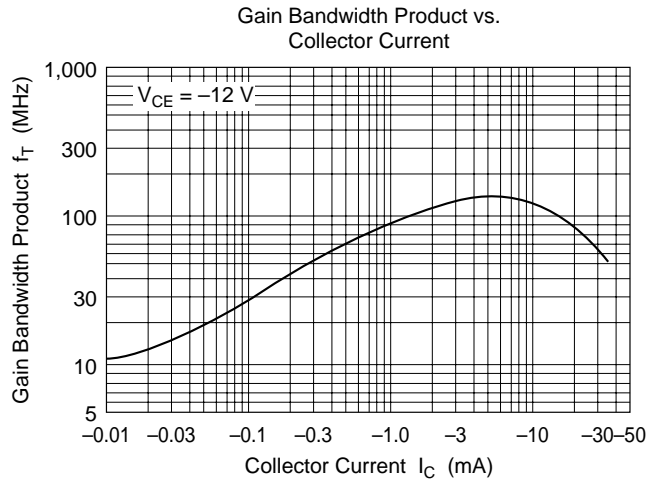
Item	Symbol	2SB715			2SB716			2SB716A			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-100	—	—	-120	—	—	-140	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-100	—	—	-120	—	—	-140	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Collector cutoff current	I_{CBO}	—	—	-0.5	—	—	—	—	—	—	μA	$V_{CB} = -80 \text{ V}, I_E = 0$
		—	—	—	—	—	-0.5	—	—	-0.5	μA	$V_{CB} = -100 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	250	—	800	250	—	800	250	—	500		$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
	h_{FE2}	125	—	—	125	—	—	125	—	—		$V_{CE} = -12 \text{ V}, I_C = -10 \text{ mA}$
Base to emitter voltage	V_{BE}	—	—	-0.75	—	—	-0.75	—	—	-0.75	V	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.2	—	—	-0.2	—	—	-0.2	V	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$
Gain bandwidth product	f_T	—	150	—	—	150	—	—	150	—	MHz	$V_{CE} = -12 \text{ V}, I_C = -5 \text{ mA}$
Collector output capacitance	C_{ob}	—	1.8	—	—	1.8	—	—	1.8	—	pF	$V_{CB} = -25 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

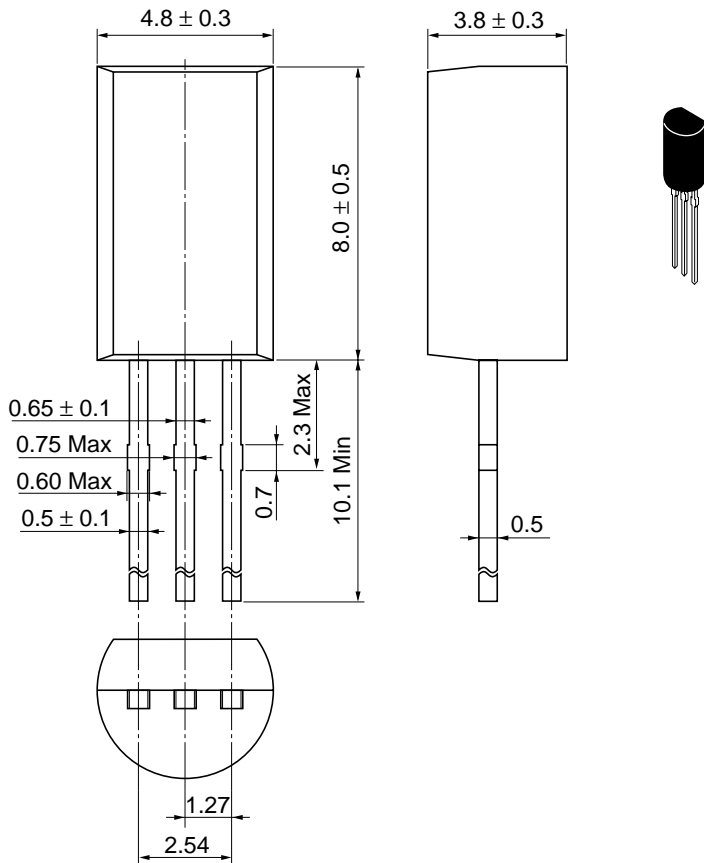
Note: 1. The 2SB715, 2SB716 and 2SB716A are grouped by h_{FE1} as follows.

	D	E
2SB715, 2SB716	250 to 500	400 to 800
2SB716A	250 to 500	—



2SB715, 2SB716, 2SB716A





Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.35 g

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